

Appl. No. 10/694,684
Response dated 08/29/2005
Reply to Office Action 06/01/2005

Attorney Docket No.: TS02-1193
N1085-90160

Amendments to the Claims:

This Listing of Claims will replace all prior versions and listings of claims in this Application.

1 1. (Currently Amended) A method of forming a MIM capacitor, comprising the
2 steps of:

3 forming a capacitance trench within a dielectric layer formed over a substrate; the
4 capacitance trench having opposing side walls and a bottom;

5 forming respective bottom electrodes along the opposing side walls;

6 forming a capacitance dielectric layer along the respective bottom electrodes;

7 forming at least one dual damascene opening adjacent an associated one of the
8 bottom electrodes that exposes portions of an underlying metal structure; and

9 depositing metal a) in the at least one dual damascene opening that laterally
10 contacts the associated bottom electrode and b) filling the capacitor trench; and

11 planarizing to form planarized metal portions within the dual damascene
12 openings[[:]] and the capacitance trench, the metal portions within the capacitance trench
13 forming to form a top electrode of the MIM capacitor.

1 2. (Currently Amended) The method of claim 1, further comprising forming the
2 dielectric layer over the an underlying metal structure and forming a top layer over the dielectric
3 layer prior to said forming a capacitance trench, and wherein

4 the capacitance trench is formed to extend through the top layer,

5 the capacitance dielectric layer is further formed along the bottom of the
6 capacitance trench and remaining portions of the top layer, [[and]]

7 forming at least one dual damascene opening comprises forming initial via
8 openings adjacent the capacitance trench then forming respective trench openings above,
9 continuous and contiguous with lower portions of the respective via openings to form respective
10 opposing ones of said at least one dual damascene opening and,

11 each said dual damascene opening exposes portions of the metal structure.

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1 3. (Previously Presented) The method of claim 2, wherein the metal structure
2 is comprised of copper, aluminum or gold; the dielectric layer is comprised of an oxide material
3 having a dielectric constant of less than about 3.0, silicon oxide or FSG; the top layer is
4 comprised of silicon oxynitride; the bottom electrodes are comprised of TaN or TiN; the
5 capacitance dielectric layer is comprised of oxide or silicon oxide; and the planarized metal
6 portions are comprised of copper, aluminum or gold.

1 4. (Previously Presented) The method of claim 2, wherein the metal structure
2 is comprised of copper; the dielectric layer is comprised of an oxide material having a dielectric
3 constant of less than about 3.0; the top layer is comprised of silicon oxynitride; the bottom
4 electrodes are comprised of TaN or TiN; the capacitance dielectric layer is comprised of oxide;
5 and the planarized metal portions are comprised of copper.

1 5. (Previously Presented) The method of claim 2, wherein the metal structure
2 has a thickness of from about 1000 to 9000Å; the dielectric layer has a thickness of from about
3 2000 to 12,000Å; the top layer has a thickness of from about 300 to 1500Å; the bottom
4 electrodes have a thickness of from about 100 to 500Å; and the capacitance dielectric layer has a
5 thickness of from about 100 to 600Å.

1 6. (Previously Presented) The method of claim 2, wherein the metal structure
2 has a thickness of from about 2000 to 8000Å; the dielectric layer has a thickness of from about
3 7000 to 9000Å; the top layer has a thickness of from about 1000 to 14,000Å; the bottom
4 electrodes have a thickness of from about 200 to 400Å; and the capacitance dielectric layer has a
5 thickness of from about 250 to 350Å.

1 7. (Currently Amended) The method of claim 2, further including the step of
2 forming [[a]] an etch stop layer between the metal structure and the dielectric layer.

1 8. (Currently Amended) The method of claim 1, further including the step of
2 forming [[a]] an etch stop layer between the metal structure and the dielectric layer; the etch stop
3 layer being comprised of silicon nitride or silicon carbide and having a thickness of from about
4 300 to 900Å.

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1 9. (Currently Amended) The method of claim 1, further including the step of
2 forming ~~[[a]]~~ an etch stop layer between the metal structure and the dielectric layer; the etch stop
3 layer ~~being~~ comprised of silicon nitride or silicon carbide and having a thickness of ~~from~~ about
4 400 to 600Å.

1 10. (Previously Presented) The method of claim 2, wherein the initial via openings
2 expose portions of the metal structure.

1 11. (Original) The method of claim 1, further including a top metal process.

1 12. (Currently Amended) A method of forming a MIM capacitor, comprising the
2 sequential steps of:

3 providing a structure having a metal structure formed thereover; the metal
4 structure being comprised of copper, aluminum or gold;

5 forming a dielectric layer over the metal structure; the dielectric layer being
6 comprised of an oxide material having a dielectric constant of less than about 3.0, such as silicon
7 oxide or FSG;

8 forming a top layer over the dielectric layer; the top layer being comprised of
9 silicon oxynitride;

10 forming a capacitance trench through the top layer and into the dielectric layer;
11 the capacitance trench have opposing side walls and a bottom;

12 forming respective bottom electrodes over the capacitance trench opposing side
13 walls; the bottom electrodes being comprised of TaN or TiN;

14 forming a capacitance dielectric layer over the respective bottom electrodes, the
15 bottom of the capacitance trench; and ~~[[the]]~~ remaining portions of the top layer; the capacitance
16 dielectric layer being comprised of oxide or silicon oxide;

17 forming respective opposing initial via openings adjacent the capacitance trench;

18 forming respective trench openings above, continuous and contiguous with ~~[[the]]~~
19 lower portions of the respective opposing initial via openings and exposing portions of the
20 underlying metal structure and the respective bottom electrodes to form respective opposing dual
21 damascene openings; and

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22 forming planarized metal portions within the dual damascene openings
23 and the capacitance trench to form a top electrode,
24 the planarized metal portions being comprised of copper, aluminum or gold; to
25 complete formation of the MIM capacitor.

1 13. (Original) The method of claim 12, wherein the structure is a silicon substrate, a
2 germanium substrate, a semiconductor wafer or a semiconductor substrate.

1 14. (Original) The method of claim 12, wherein the metal structure is comprised of
2 copper; the dielectric layer is comprised of an oxide material having a dielectric constant of less
3 than about 3.0; the top layer is comprised of silicon oxynitride; the bottom electrodes are
4 comprised of TaN or TiN; the capacitance dielectric layer is comprised of oxide; and the
5 planarized metal portions are comprised of copper.

1 15. (Original) The method of claim 12, wherein the metal structure has a thickness of
2 from about 1000 to 9000Å; the dielectric layer has a thickness of from about 2000 to 12,000Å;
3 the top layer has a thickness of from about 300 to 1500Å; the bottom electrodes have a thickness
4 of about 100 to 500Å; and the capacitance dielectric layer has a thickness of from about 100 to
5 600Å.

1 16. (Original) The method of claim 12, wherein the metal structure has a thickness of
2 from about 2000 to 8000Å; the dielectric layer has a thickness of from about 7000 to 9000Å; the
3 top layer has a thickness of from about 1000 to 14,000Å; the bottom electrodes have a thickness
4 of from about 200 to 400Å; and the capacitance dielectric layer has a thickness of from about
5 250 to 350Å.

1 17. (Currently Amended) The method of claim 12, including the step of forming [a]
2 an etch stop layer between the metal structure and the dielectric layer.

1 18. (Currently Amended) The method of claim 12, including the step of forming [a]
2 an etch stop layer between the metal structure and the dielectric layer; the etch stop layer being
3 comprised of silicon nitride or silicon carbide and having a thickness of from about 300 to 900Å.

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1 19 (Currently Amended) The method of claim 12, including the step of forming [[a]]
2 an etch stop layer between the metal structure and the dielectric layer; the etch stop layer being
3 comprised of silicon nitride or silicon carbide and having a thickness of from about 400 to 600Å.

1 20 (Original) The method of claim 12, wherein the initial via openings expose
2 portions of the metal structure.

1 21. (Original) The method of claim 12, further including a top metal process.

1 22. (Withdrawn) A vertical MIM capacitor, comprising:
2 a bottom structure having a metal structure formed thereover;
3 a patterned dielectric layer over the metal structure;
4 a metal-insulator-metal structure within the patterned dielectric layer; the metal-
5 insulator-metal structure having a first and second opposing sides;
6 a first planarized metal portion adjacent the metal-insulator-metal structure on the
7 first opposing side; the first planarized metal portion being in electrical connection with the
8 metal structure;
9 a second planarized metal portion adjacent the metal-insulator-metal structure on
10 the second opposing side;
11 an inter-metal dielectric layer over the metal-insulator-metal structure and the first
12 and second planarized metal portion; and
13 a contact within the inter-metal dielectric layer in electrical contact with the
14 second planarized metal portion.

1 23 (Withdrawn) The structure of claim 22, wherein the bottom structure is a silicon
2 substrate, a germanium substrate, a semiconductor wafer or a semiconductor substrate.

1 24. (Withdrawn) The structure of claim 22, wherein the metal structure is comprised
2 of copper, aluminum or gold; the patterned dielectric layer is comprised of an oxide material
3 having a dielectric constant of less than about 3.0, silicon oxide or FSG; and the planarized metal
4 portions are comprised of copper, aluminum or gold.

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1 25. (Withdrawn) The structure of claim 22, wherein the metal structure is comprised
2 of copper; the dielectric layer is comprised of an oxide material having a dielectric constant of
3 less than about 3.0; and the planarized metal portions are comprised of copper.

1 26. (Withdrawn) The structure of claim 22, wherein the metal structure has a
2 thickness of from about 1000 to 9000Å; and the patterned dielectric layer has a thickness of from
3 about 2000 to 12,000Å.

1 27. (Withdrawn) The structure of claim 22, wherein the metal structure has a
2 thickness of from about 2000 to 8000Å; and the dielectric layer has a thickness of from about
3 7000 to 9000Å.

1 28. (Withdrawn) The structure of claim 22, including a pair of respective bottom
2 electrodes interposed between the metal-insulator-metal structure and the first and second
3 planarized metal portions.

1 29. (Withdrawn) The structure of claim 22, including a pair of respective bottom
2 electrodes interposed between the metal-insulator metal structure and the first and second
3 planarized metal portions; the pair of respective bottom electrodes each being comprised of TaN
4 or TiN and having a thickness of from about 100 to 500Å.

1 30. (Withdrawn) The structure of claim 22, including a pair of respective bottom
2 electrodes interposed between the metal-insulator-metal structure and the first and second
3 planarized metal portions; the pair of respective bottom electrodes each being comprised of TaN
4 and TiN and having a thickness of from about 200 to 400Å.

1 31. (Currently Amended) The method of claim 1, wherein the structure substrate is a
2 silicon substrate, a germanium substrate, a semiconductor wafer or a semiconductor substrate